

Article | Published: 13 August 2018

# Superconducting, insulating and anomalous metallic regimes in a gated two-dimensional semiconductor–superconductor array

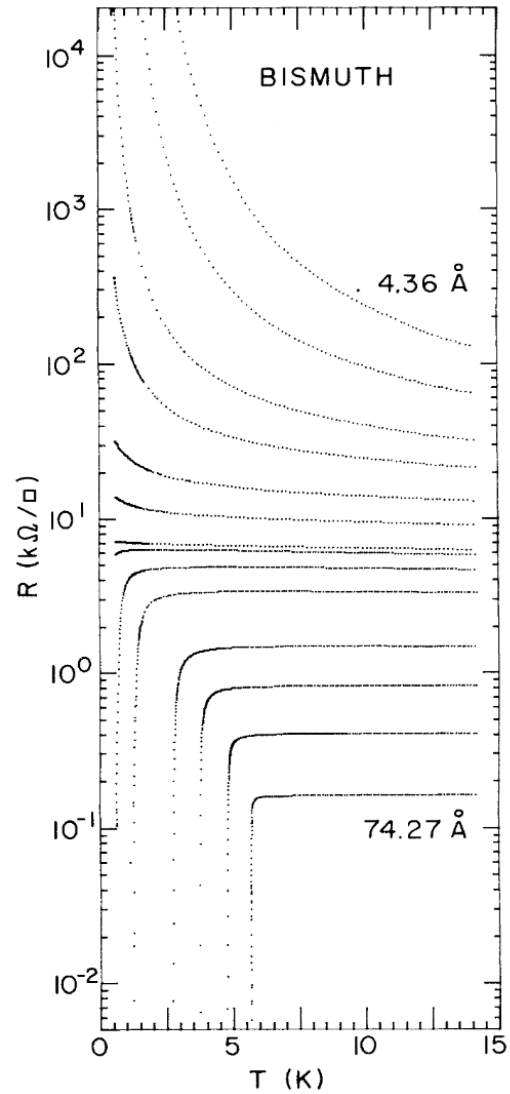
C. G. L. Bøttcher, F. Nichele, M. Kjaergaard, H. J. Suominen, J. Shabani, C. J. Palmstrøm & C. M. Marcus 

*Nature Physics* **14**, 1138–1144(2018) | [Cite this article](#)

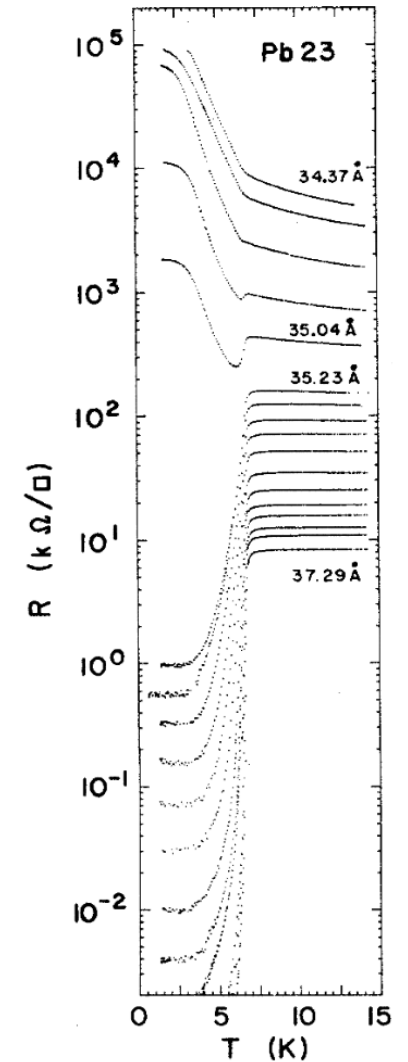
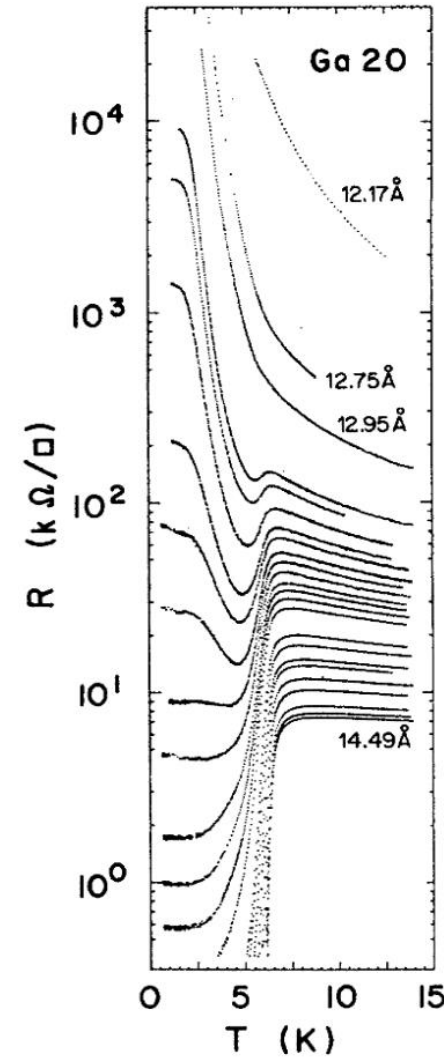
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Journal Club Presentation  
**Mohammad Samani**  
October 2, 2020

# Superconductor to Insulator Transition



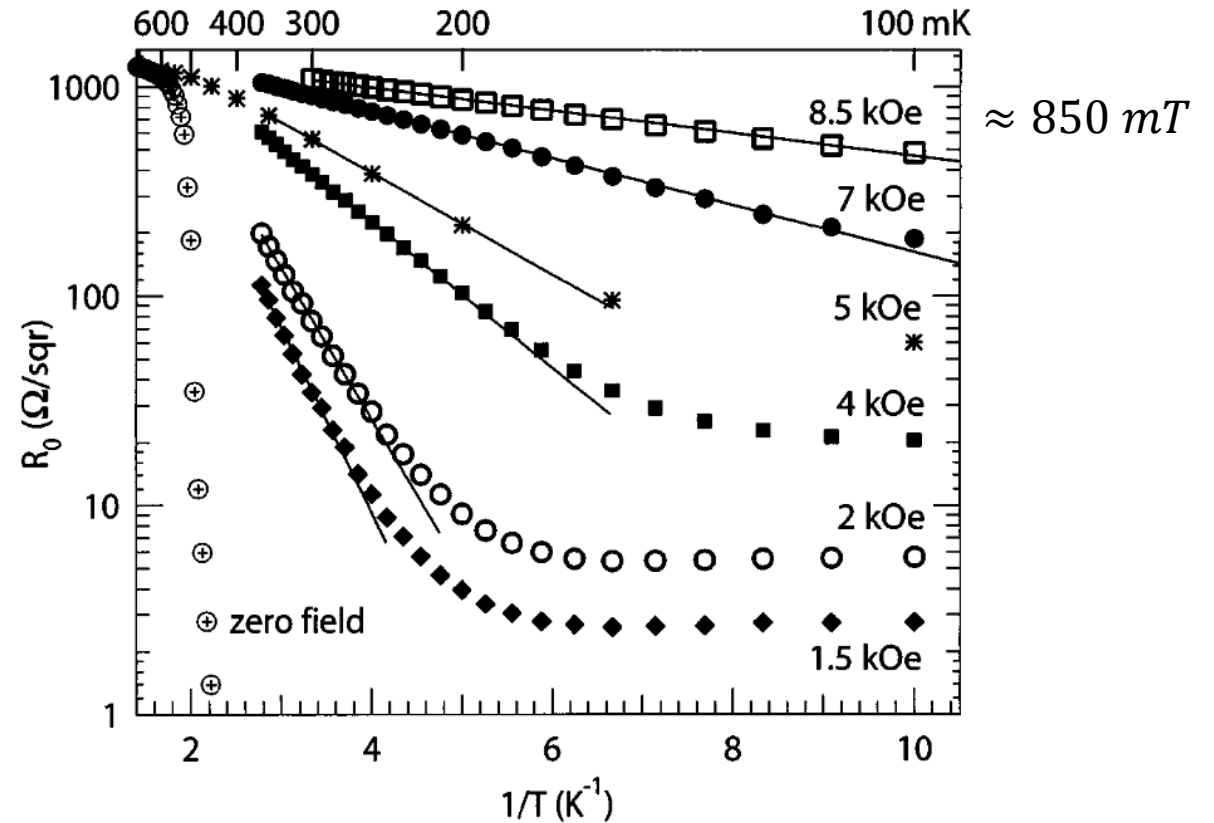
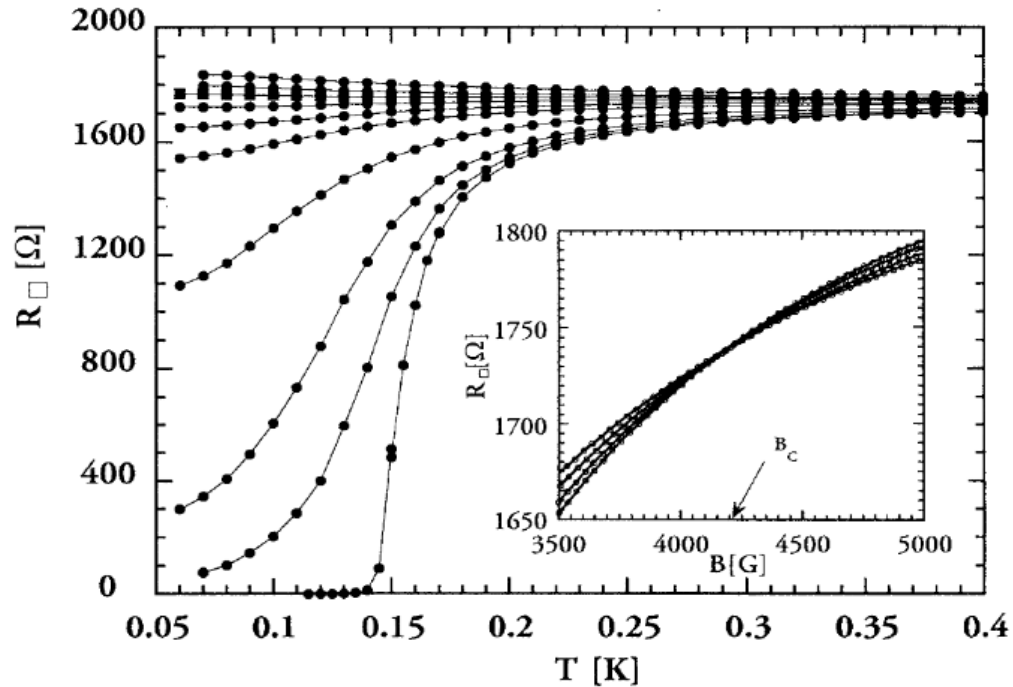
1. Phase fluctuations in SC order parameter localizes Cooper pairs
  2. Reduced SC pairing amplitude due to unscreened repulsive interactions
- => Direct phase transition from SC to Insulator



# Magnetic Field Driven

a:MoGe

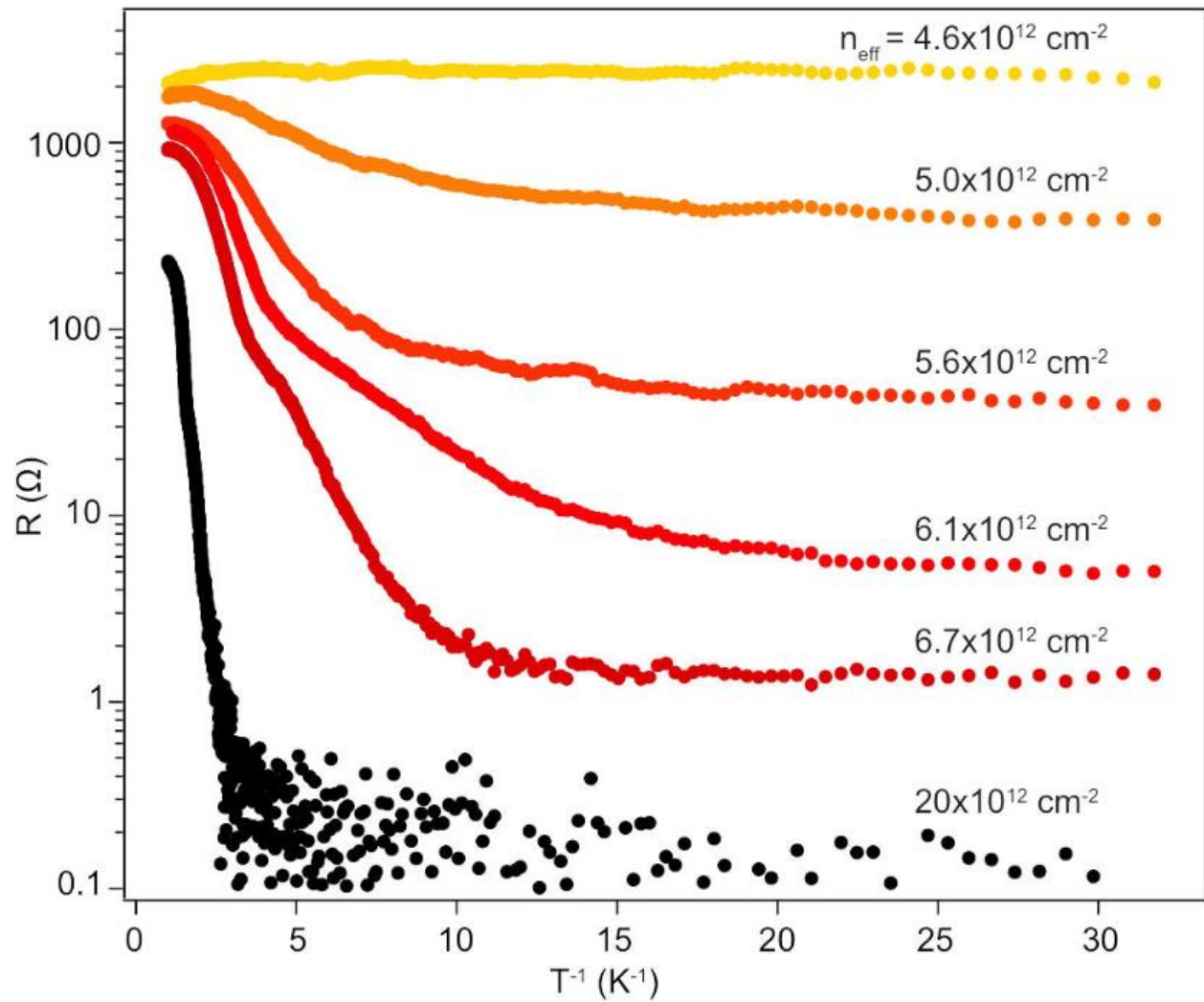
$B=0, 50, 100, 200, 300, 400, 440, 450, 550, 600$  mT



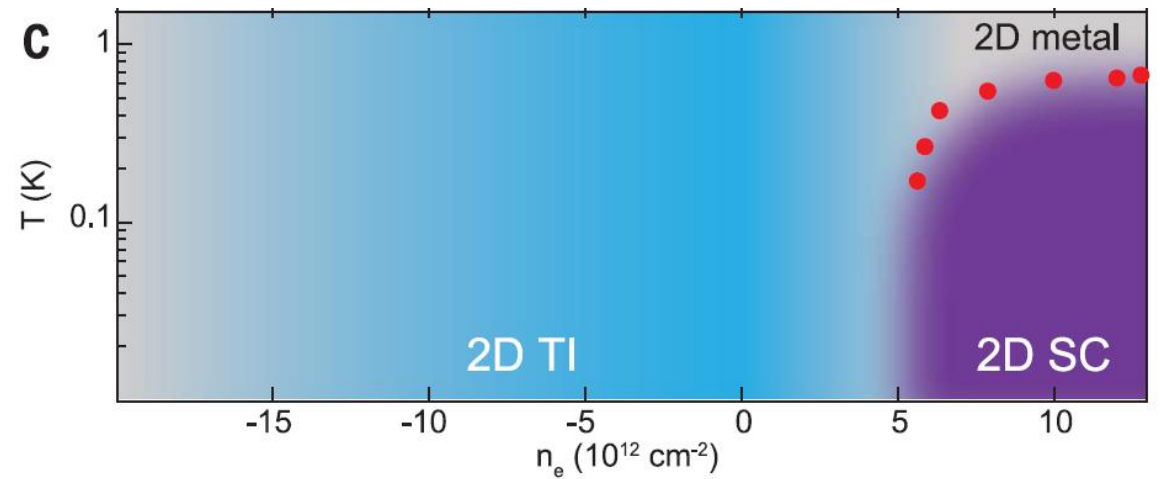
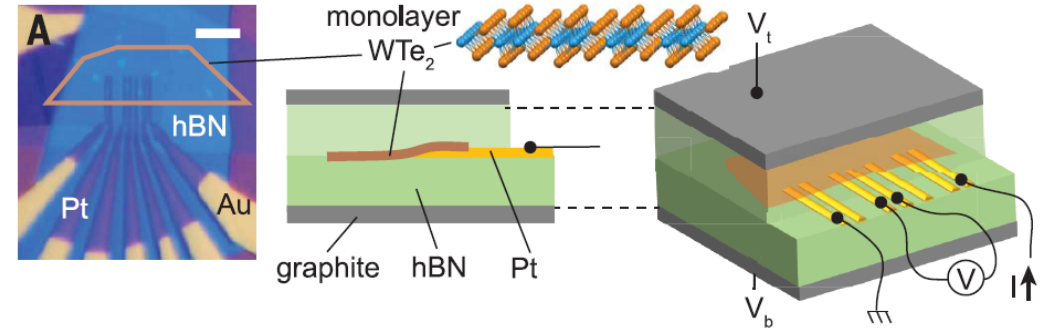
Yazdani, A. and Kapitulnik A. Phys. Rev. Lett. 74, 15 (1995)

Ephron, D. and Yazdani, A. and Kapitulnik, A. and Beasley M. R. Phys. Rev. Lett. 76, 9 (1996)

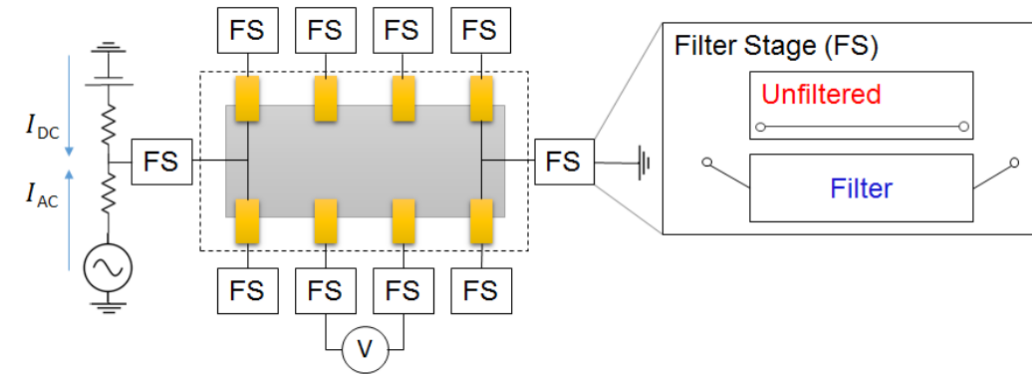
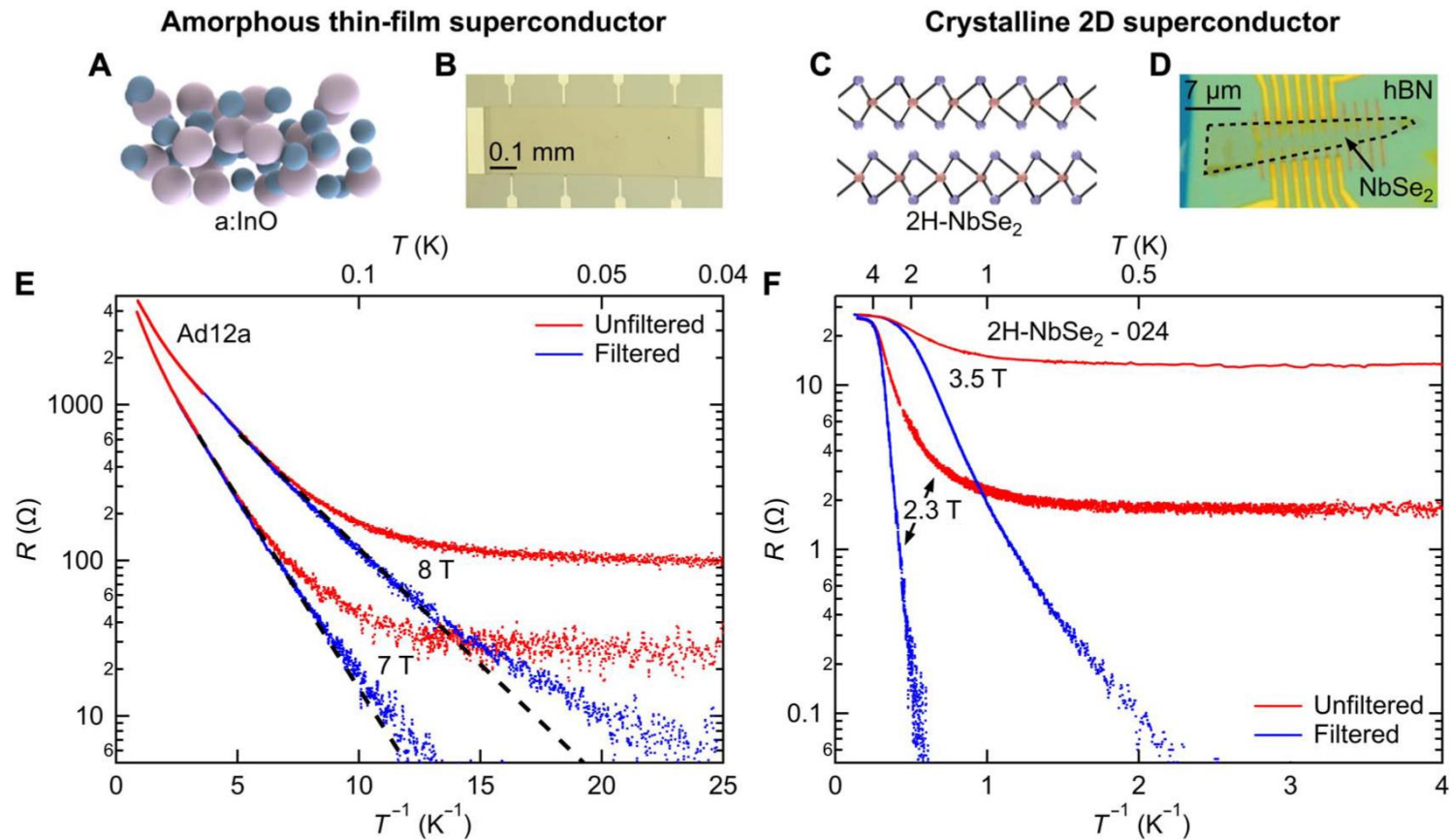
# Density Driven



WTe<sub>2</sub> monolayer film



# It's all in your head



- Homemade RC filter
- Commercial low-pass filter
- Attenuator

Sensitivity of superconductivity in 2D

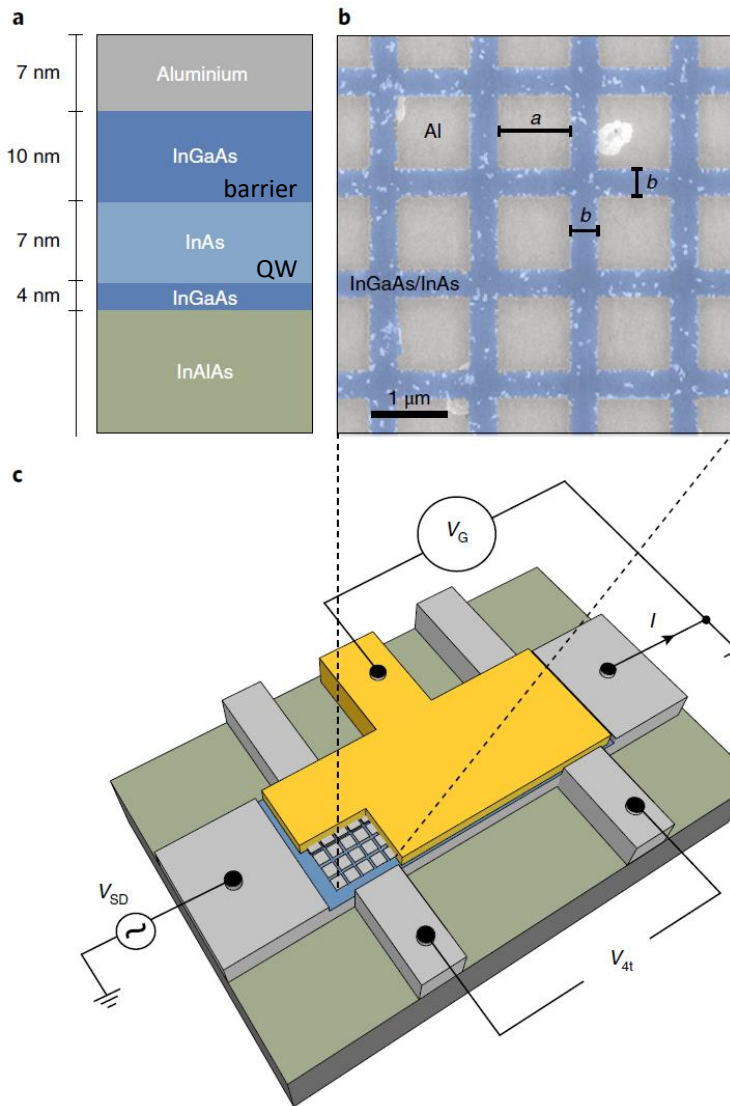
2H – NbSe<sub>2</sub>,  $B_c \approx 5.5$  T at low T



# Characteristics of Anomalous Metals

1. Most of evidence comes from 2D materials
2. Disorder, carrier density, screening properties, and magnetic field are used as tuning parameters.
3.  $\sigma_D \ll e^2/h$
4. Always an intermediate regime from superconducting to metal or insulator
5. Disorder is not necessary

# The Device



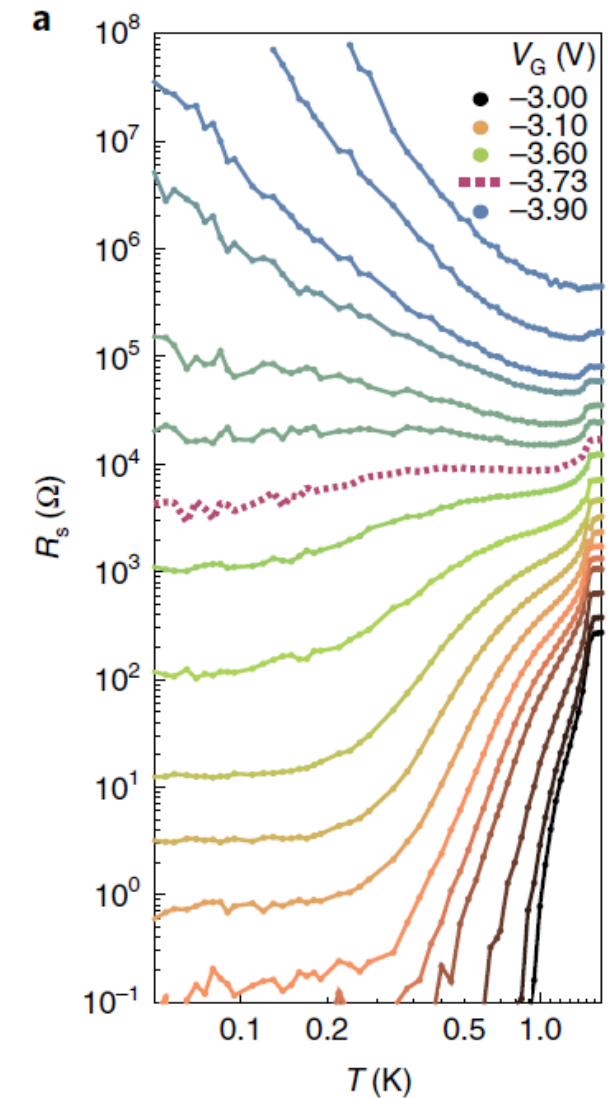
$a = 1 \mu\text{m}$   
 $b = 150 \text{ nm (A) } 350 \text{ nm (B)}$   
Mean free path = 300 nm  
40 × 100 array of aluminium squares

40 nm of Al<sub>2</sub>O<sub>3</sub> below TiAu top gate

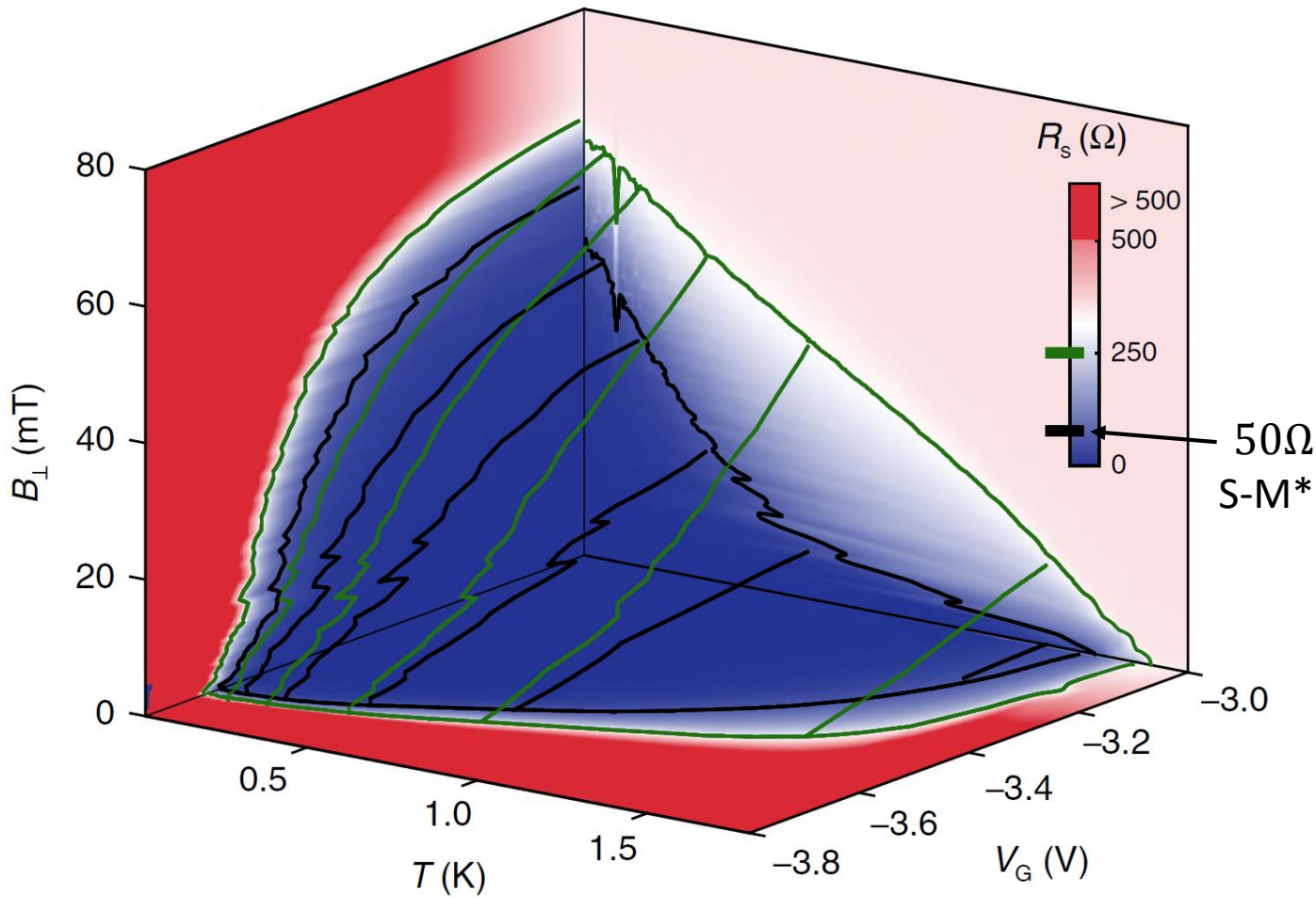
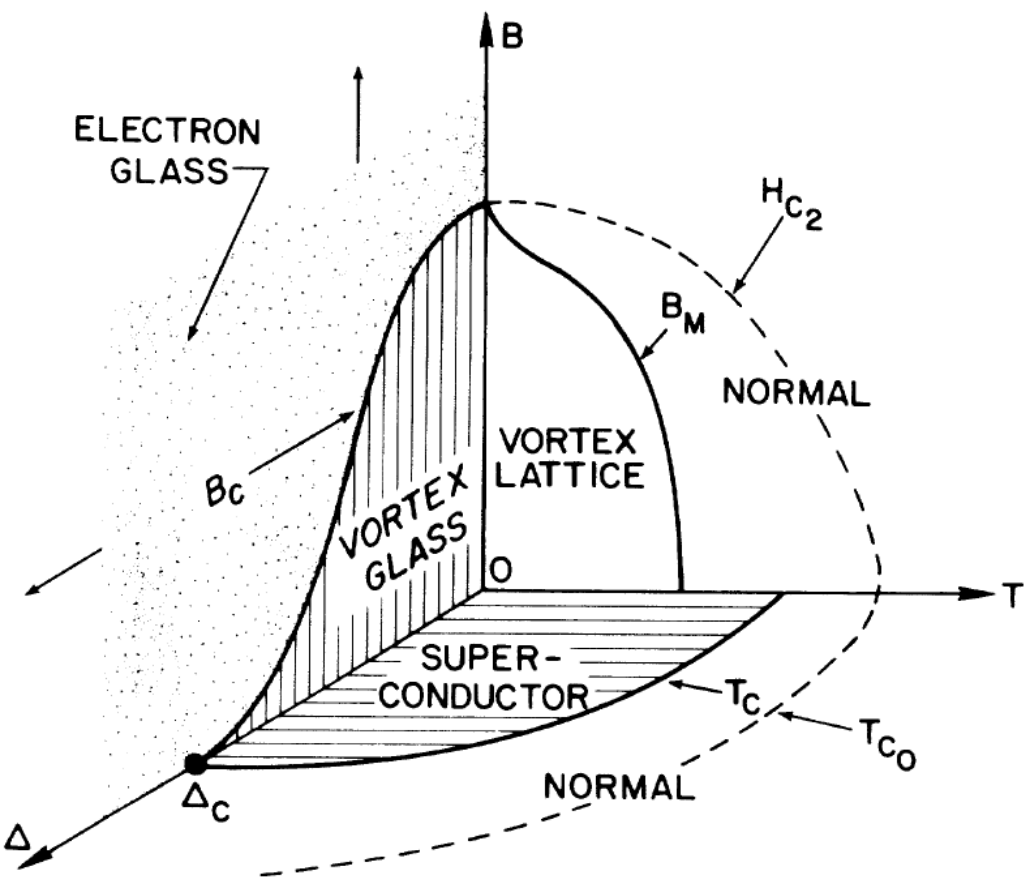
$V_{sd} \leq 5 \mu\text{V}$

Unique combination of characteristics:

1. High mobility
2. Large g-factor
3. Strong spin-orbit coupling
4. Large  $B_{\parallel}^* \approx 600 \text{ mT}$

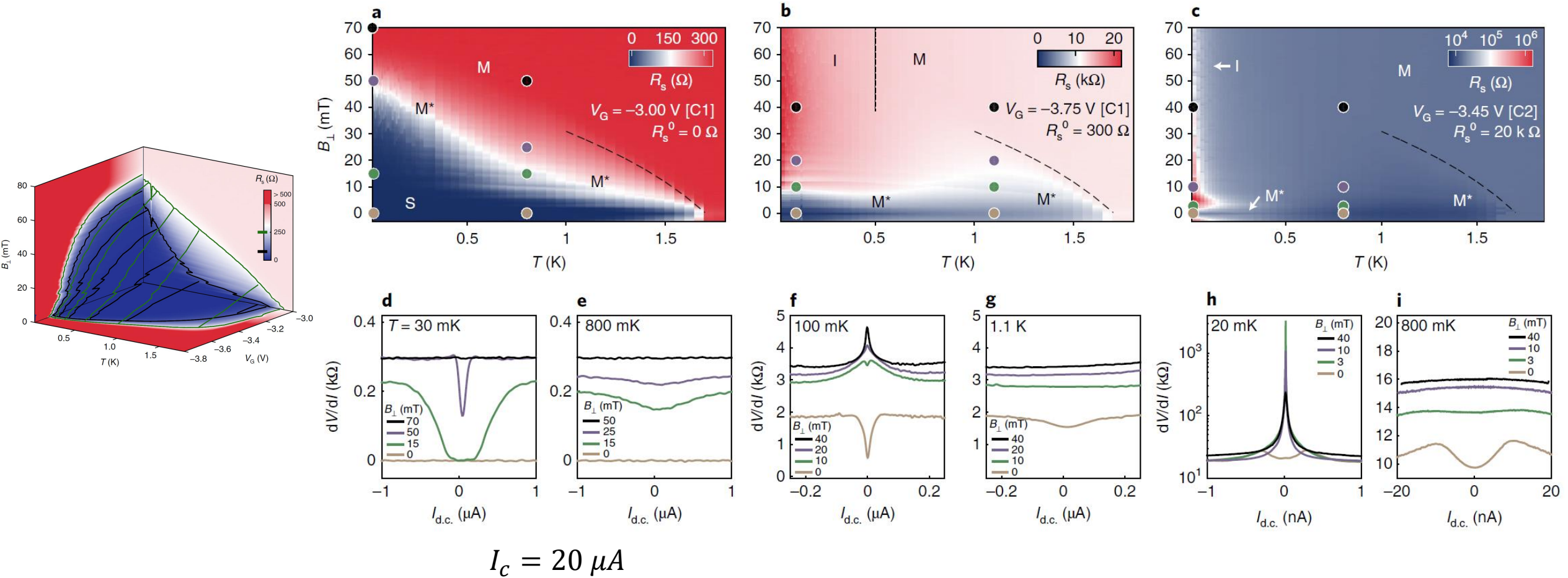


# Phase Diagram

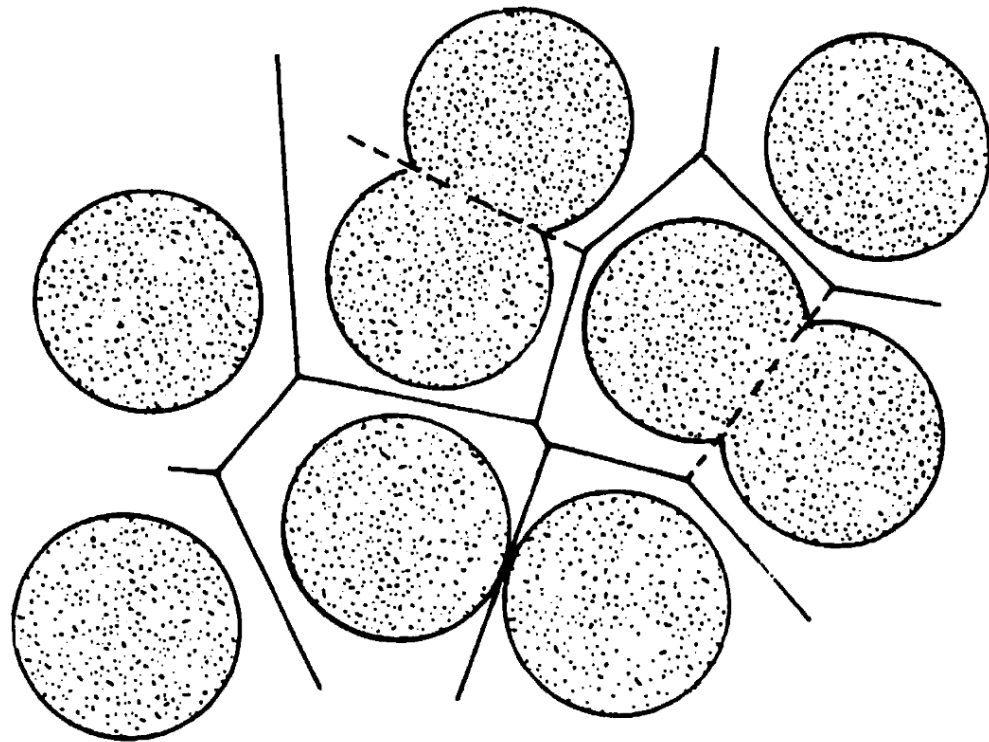




# Phase Diagram



# Classical Percolation Theory



The Swiss cheese model

$$\sigma = \sigma_D F(x)$$

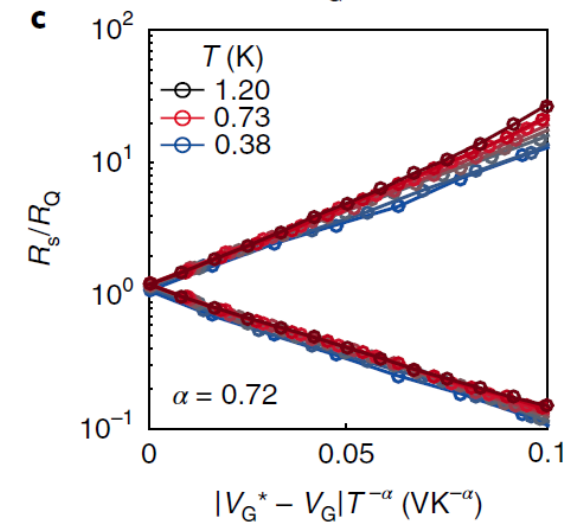
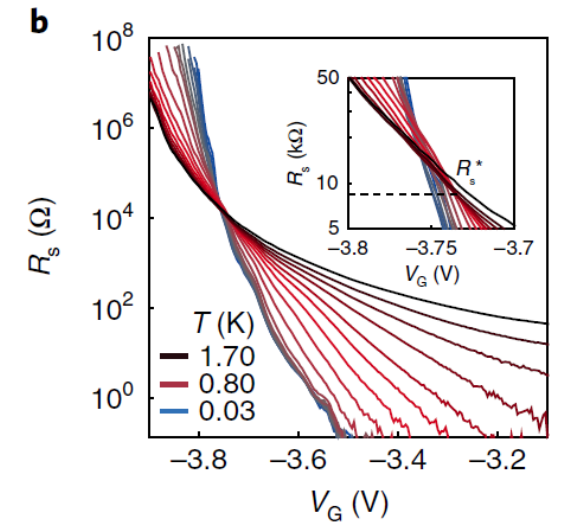
$$x \rightarrow 0 : F(x) \rightarrow 1$$

$$x \rightarrow x_c^- : F(x) \rightarrow \infty \text{ as } F(x) \sim (x_c - x)^{-s}$$

$$2D: \quad s = 4/3$$

$$3D: \quad s \sim 0.73$$

$$\alpha \sim 0.72 \Rightarrow s = 1.4$$



# Insulating Regime

$$R = R_0 e^{T_0/T}$$

$$T_0 \approx 1.5 \text{ K} \approx T_c(B = 0)$$

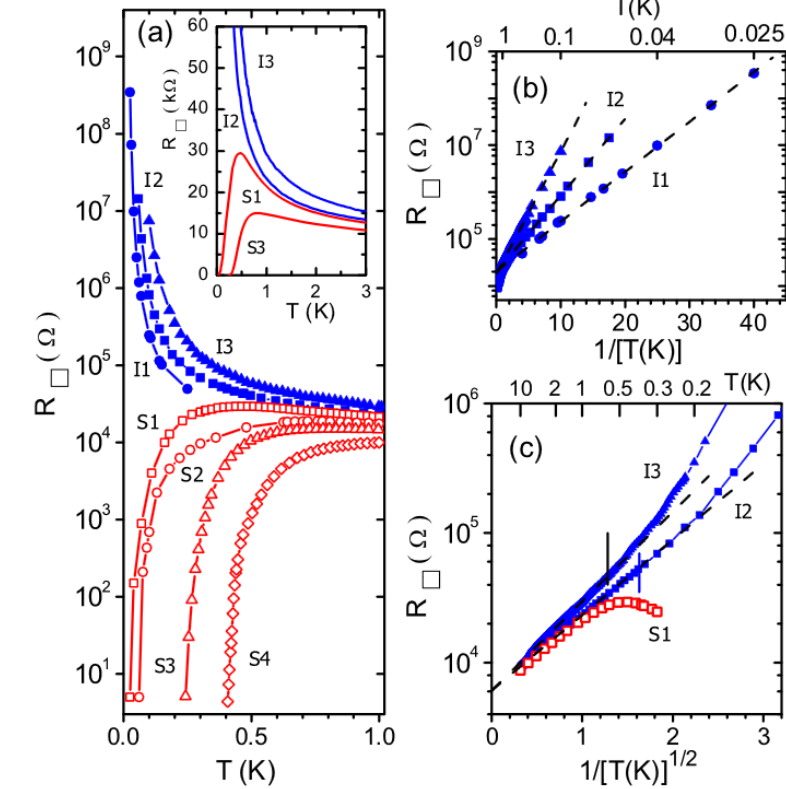
Arrhenius thermal activation

$$R = R_0 \exp[\sqrt{T_1/T}]$$

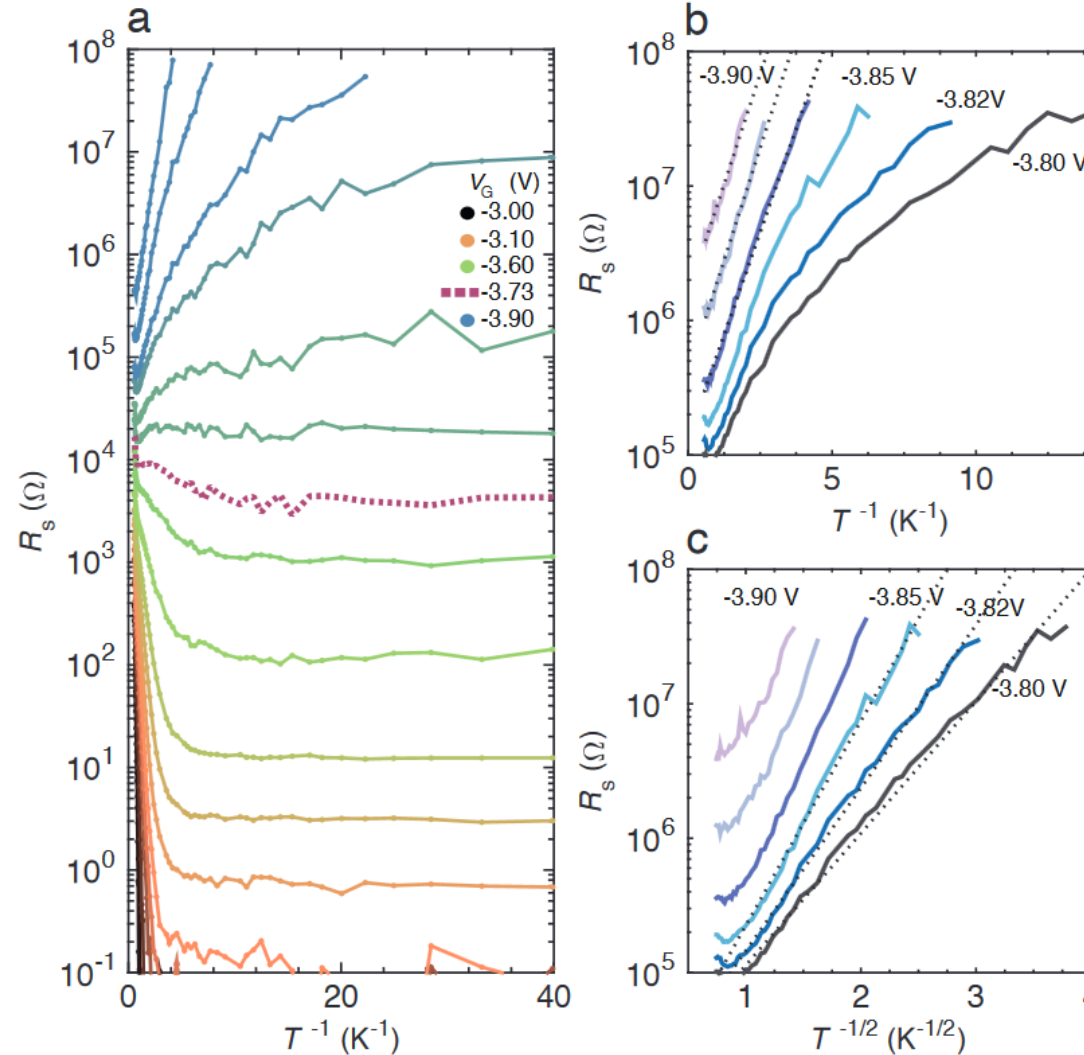
$$T_1 = 2.3, 2.5, 2.8 \text{ K}$$

Variable range hopping

Theory:  $T_1 = 3.0 \text{ K}$

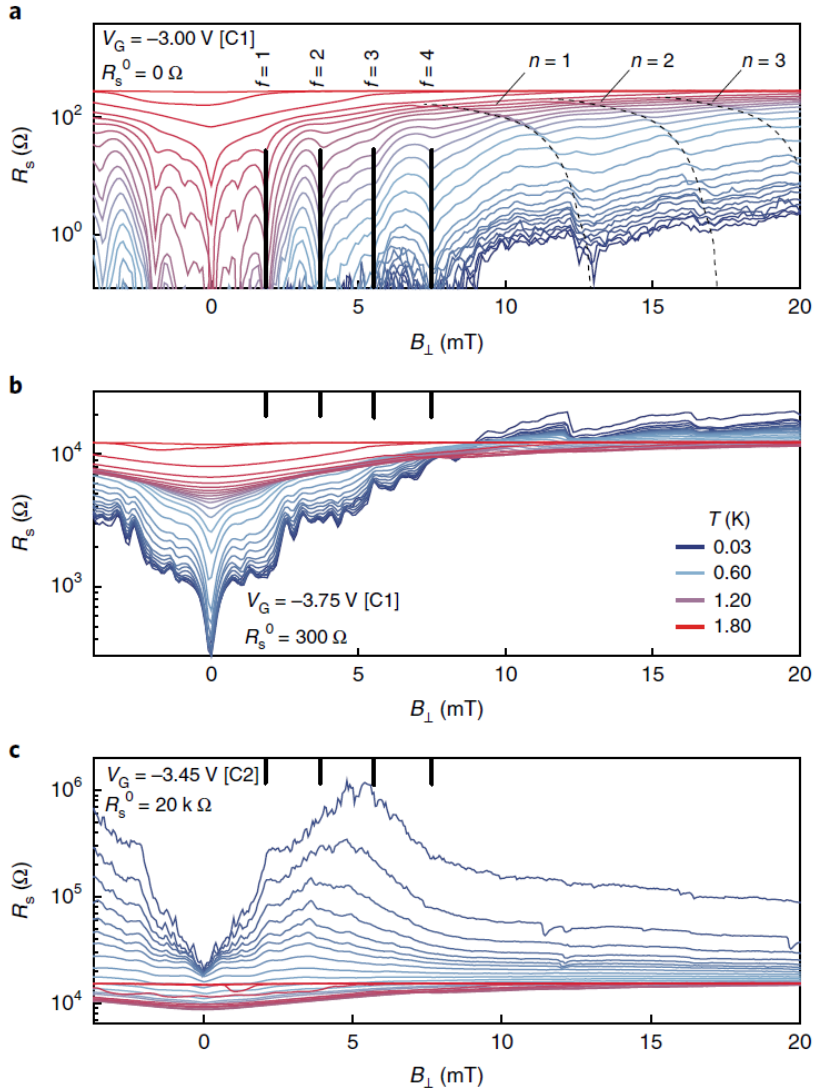


TiN superconducting films



Baturina, T. I. et Al. Phys. Rev. Lett. 99, 257003 (2007)

Efros, A. L. and Shklovskii, B. I. Properties of Doped Semiconductors (Springer, Berlin, 1984)



$$f = \frac{B_{\perp}}{B_0}, \quad B_0 = \frac{\Phi_0}{A}, \quad A = (a + b)^2, \quad \Phi_0 = h/2e$$

$B_0$  is flux quantum per period of array

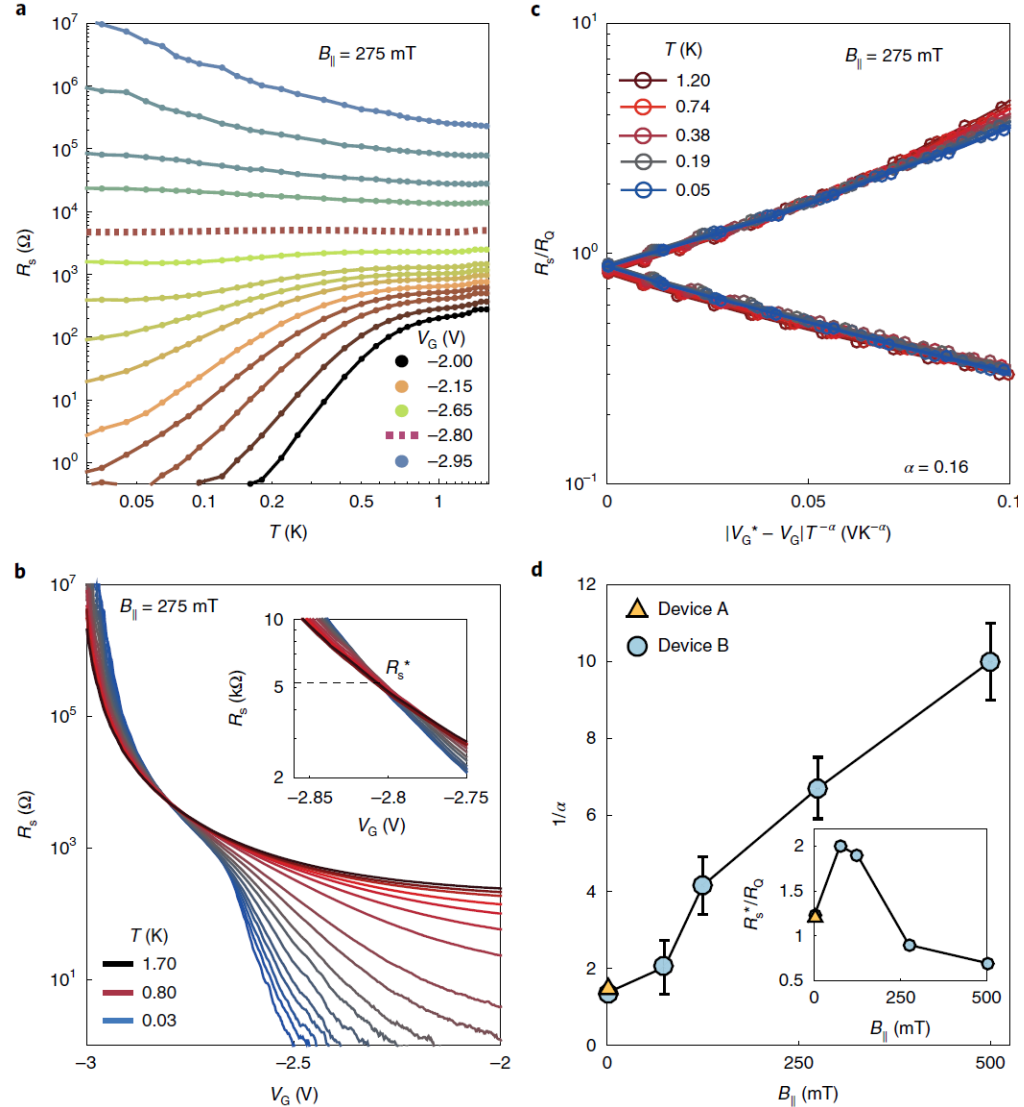
$n=1,2,3,\dots$  vortex penetration of individual islands.

1. Saturation of  $R_s$  depends on  $B_{\perp}$ , with fluctuations smaller than  $B_0 \Rightarrow$  Coherence
2. Deep saturation at  $B=0$  is a novel observation
3. Field-controlled  $R_s$  over 3 orders of magnitude  $\Rightarrow M^*$  is not due to poor filtering

0 to 5 mT changes  $R_s$  by 2 orders of magnitude. Phase disorder.  
 Compatible with Variable Range Hopping theory at finite field.



# Parallel Magnetic Field



Al layer is 7 nm, so critical in-plane field is large ( $\approx 2$  T)

Large g-factor in InAs +  
finite thickness of heterostructure:

Global superconductivity vanishes at  $B_{||}^* \approx 600$  mT

$B_{||}$  suppresses the anomalous regime quickly

Dependence of the scaling factor on B is unexplained